

Device Modeling Report

COMPONENTS: Power MOSFET (Standard)
PART NUMBER: 2SK3603-01MR
MANUFACTURER: Fuji Electric
REMARK: Body Diode (Standard)



Bee Technologies Inc.

POWER MOSFET MODEL

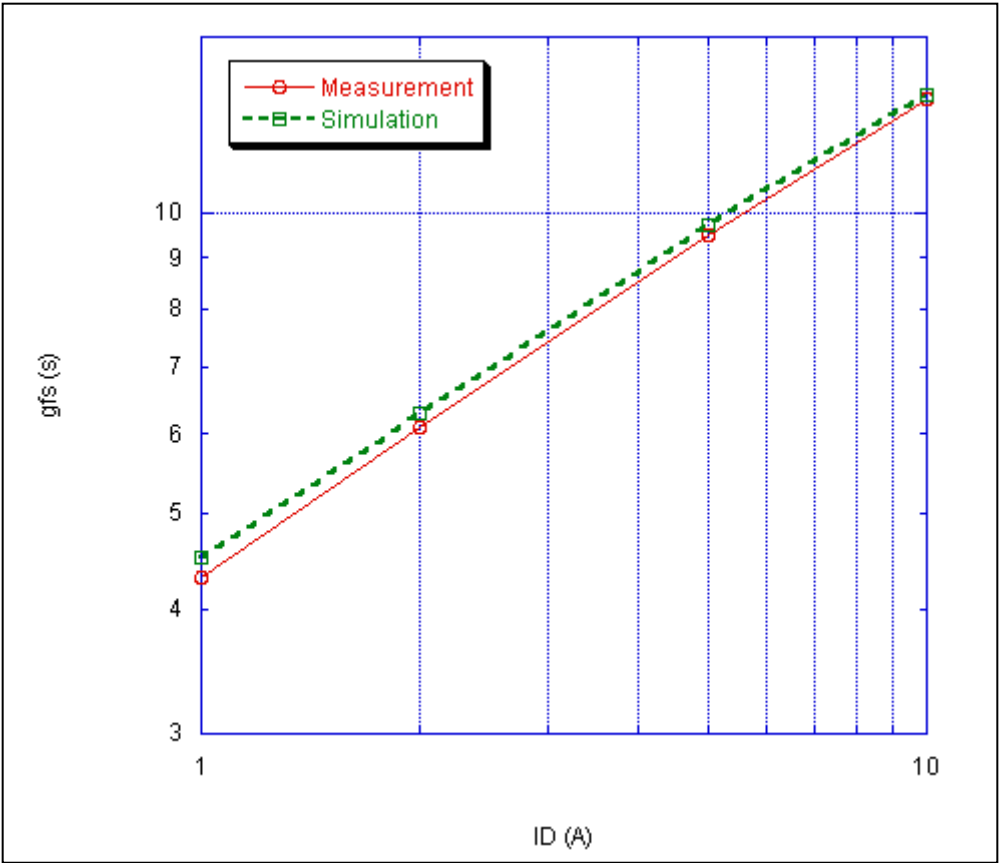
Pspice model parameter	Model description
LEVEL	
L	Channel Length
W	Channel Width
KP	Transconductance
RS	Source Ohmic Resistance
RD	Ohmic Drain Resistance
VTO	Zero-bias Threshold Voltage
RDS	Drain-Source Shunt Resistance
TOX	Gate Oxide Thickness
CGSO	Zero-bias Gate-Source Capacitance
CGDO	Zero-bias Gate-Drain Capacitance
CBD	Zero-bias Bulk-Drain Junction Capacitance
MJ	Bulk Junction Grading Coefficient
PB	Bulk Junction Potential
FC	Bulk Junction Forward-bias Capacitance Coefficient
RG	Gate Ohmic Resistance
IS	Bulk Junction Saturation Current
N	Bulk Junction Emission Coefficient
RB	Bulk Series Resistance
PHI	Surface Inversion Potential
GAMMA	Body-effect Parameter
DELTA	Width effect on Threshold Voltage
ETA	Static Feedback on Threshold Voltage
THETA	Modility Modulation
KAPPA	Saturation Field Factor
VMAX	Maximum Drift Velocity of Carriers
XJ	Metallurgical Junction Depth
UO	Surface Mobility

Body Diode Model

Pspice model parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time

Transconductance Characteristic

Circuit Simulation Result

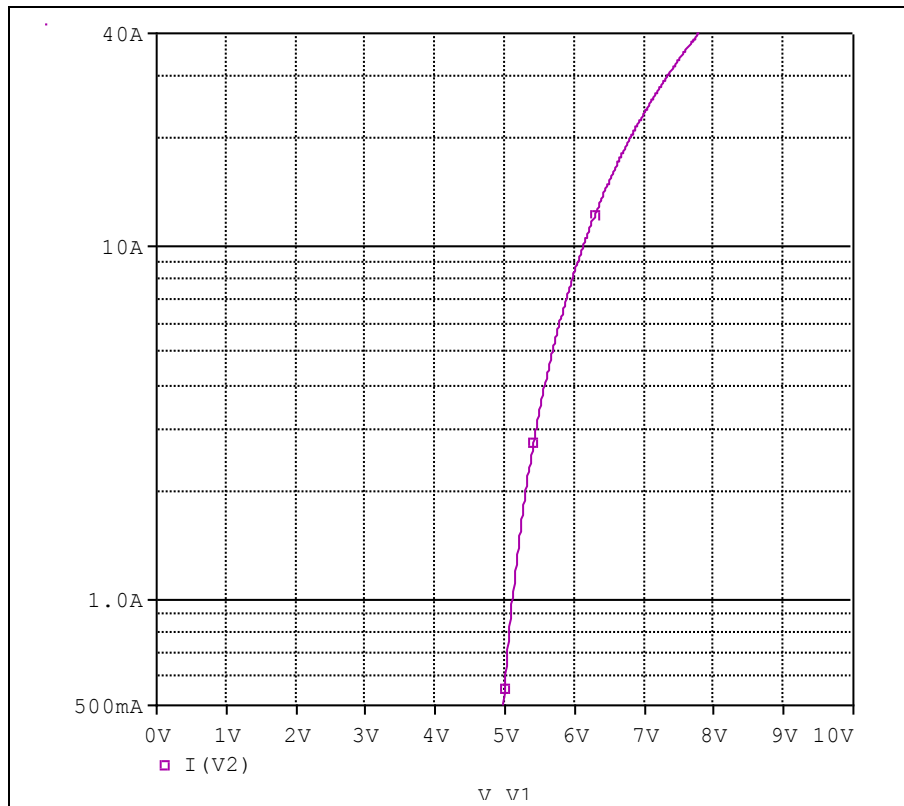


Comparison table

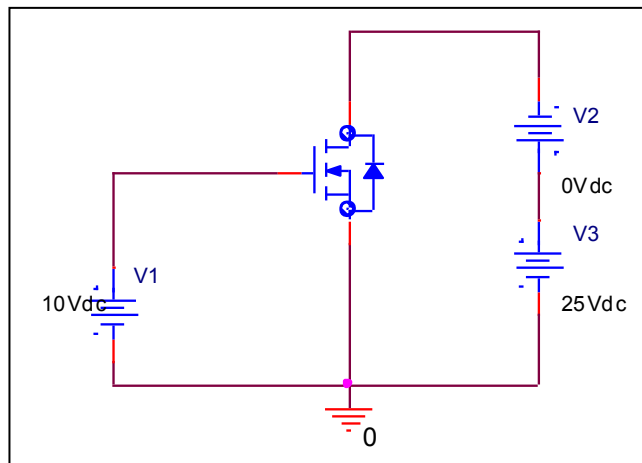
ID(A)	V _{GS} (V)		Error (%)
	Measurement	Simulation	
1	4.3	4.5	4.651
2	6.1	6.3	3.279
5	9.5	9.7	2.105
10	13	13.1	0.769

V_{gs}-I_d Characteristic

Circuit Simulation result

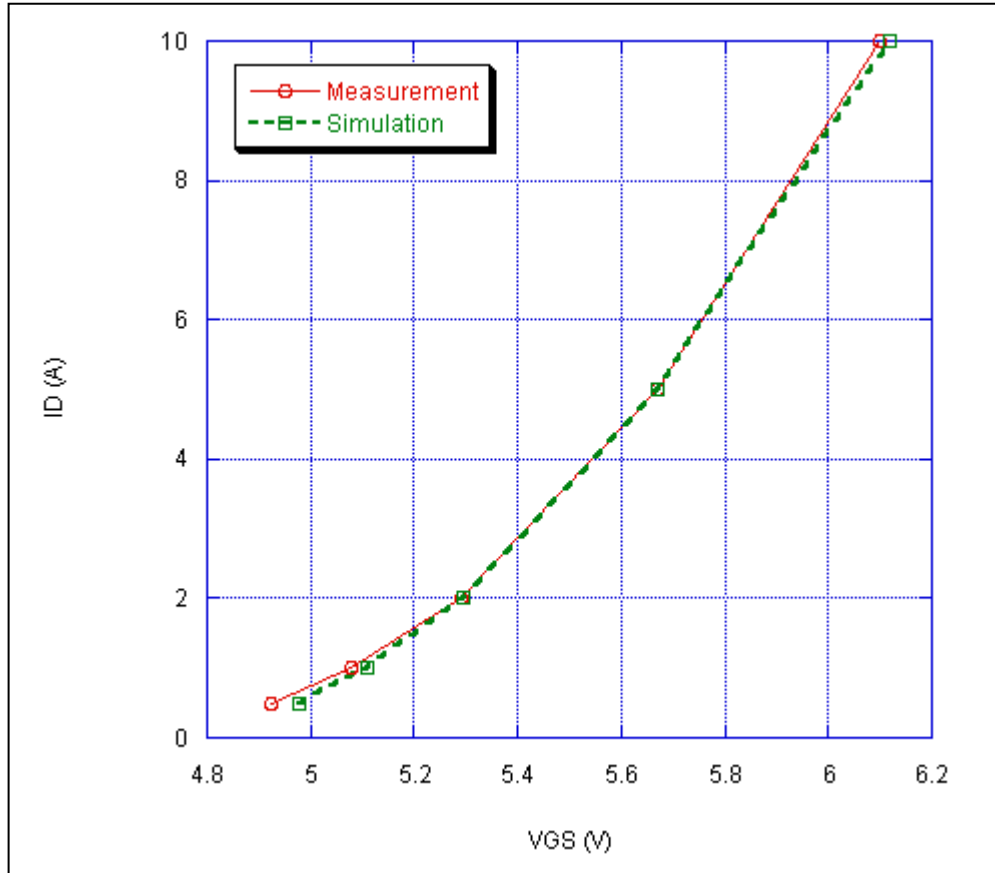


Evaluation circuit



Comparison Graph

Circuit Simulation Result

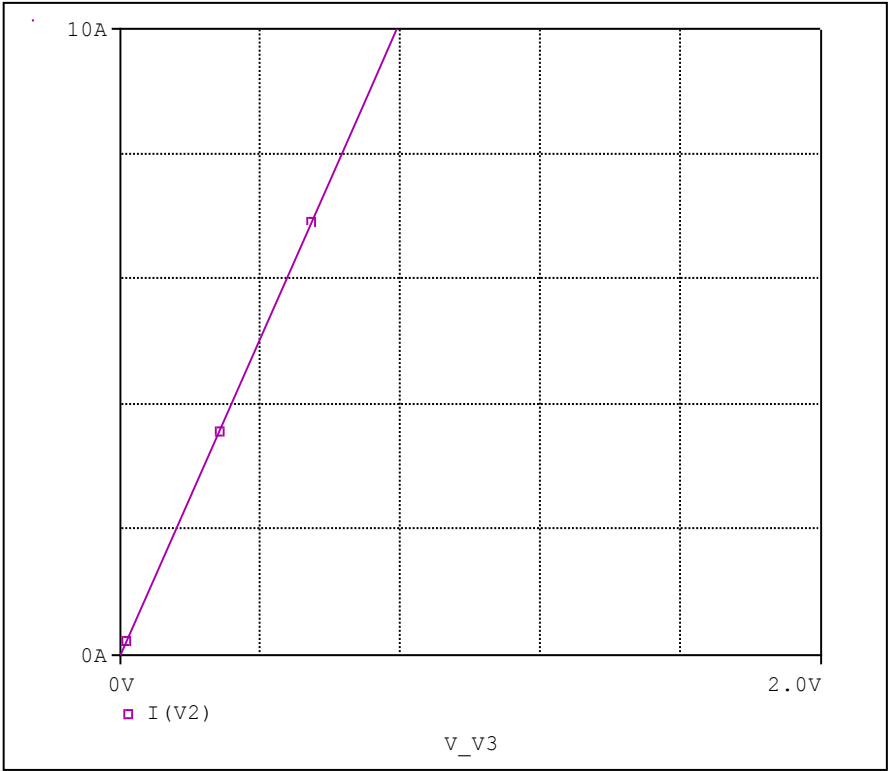


Simulation Result

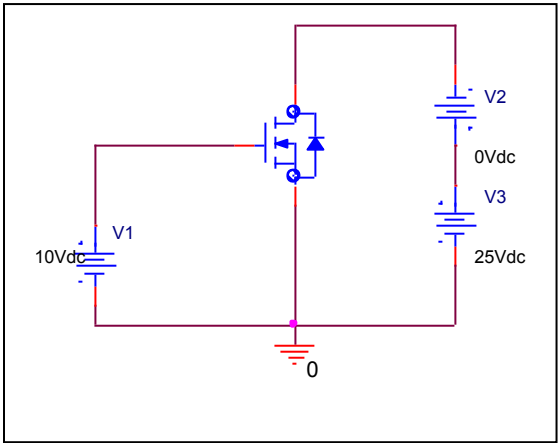
I_D (A)	V_{GS} (V)		Error (%)
	Measurement	Simulation	
0.5	4.925	4.9767	1.050
1	5.08	5.1087	0.5649
2	5.29	5.2938	0.0718
5	5.67	5.6696	-0.0070
10	6.1	6.12	0.3279

Id-Rds(on) Characteristic

Circuit Simulation result



Evaluation circuit

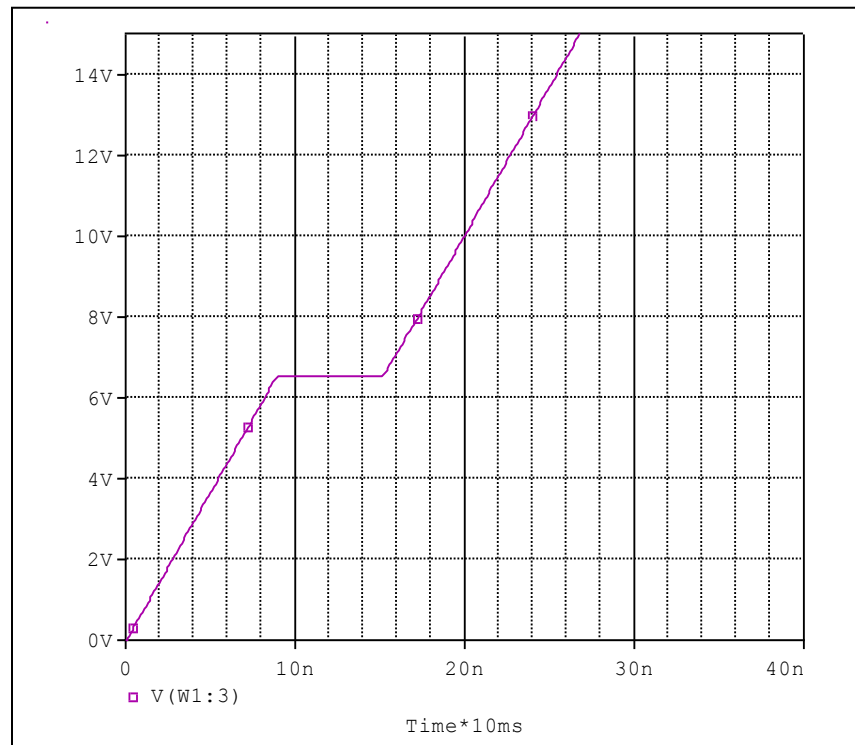


Simulation Result

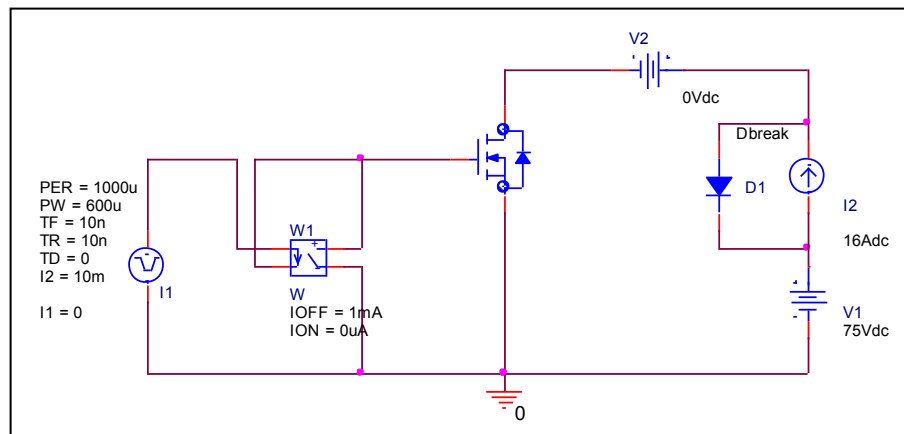
$I_D=8, V_{GS}=10V$	Measurement		Simulation		Error (%)
$R_{DS} \text{ (on)}$	79	mΩ	79.002	mΩ	0.0025

Gate Charge Characteristic

Circuit Simulation result



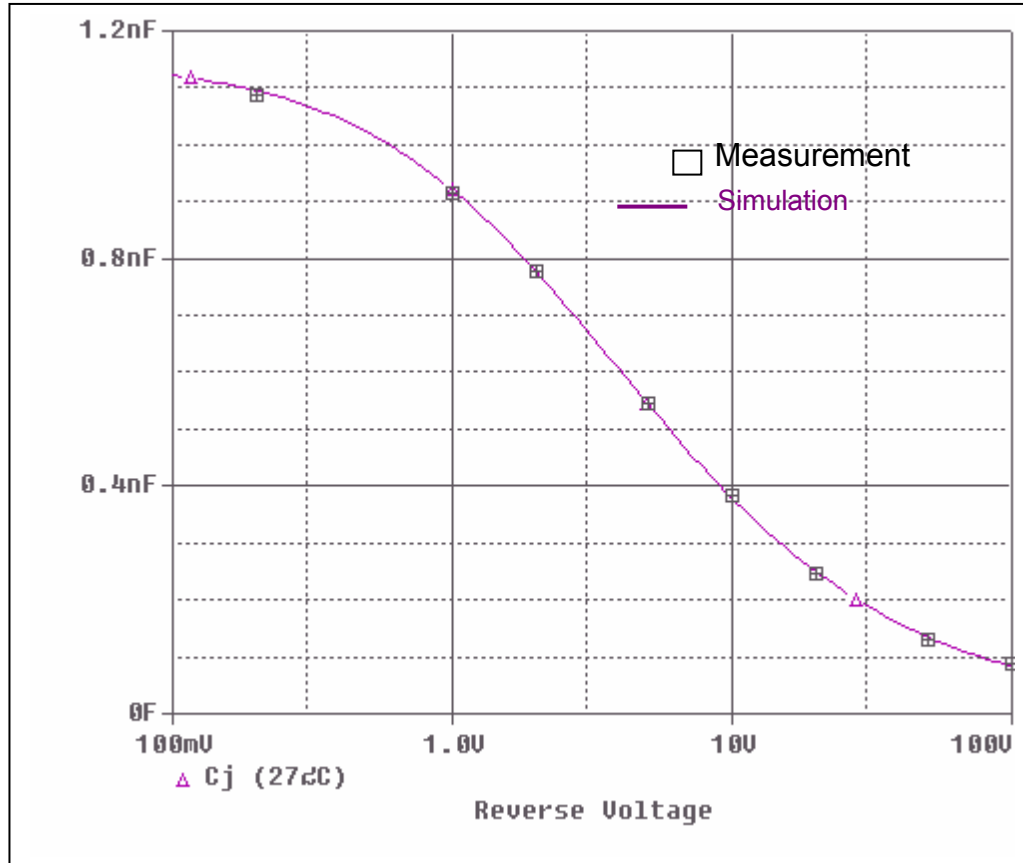
Evaluation circuit



Simulation Result

$V_{DD}=75V$ $I_D=16A$	Measurement		Simulation		Error (%)
Qgs	9	nC	9.05	nC	0.56
Qgd	6	nC	6.01	nC	0.17

Capacitance Characteristic (Vds vs. Cbd)

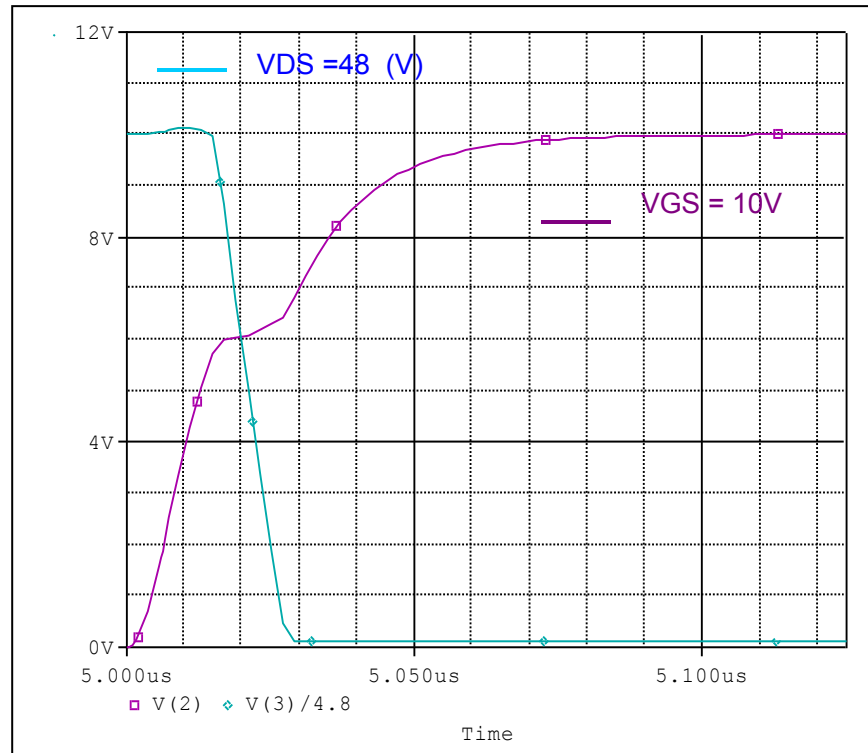


Simulation Result

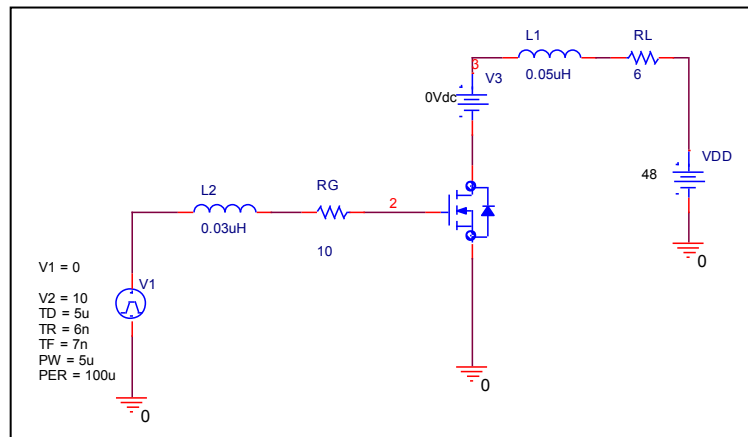
V _{DS} (V)	Cbd(pF)		Error(%)
	Measurement	Simulation	
1	920	919	-0.1087
2	780	776	-0.5128
5	550	545	-0.9091
10	387	380	-1.8088
20	250	251	0.4
50	133	135	1.5038
100	90	85	-5.5556

Switching Time Characteristic

Circuit Simulation result



Evaluation circuit

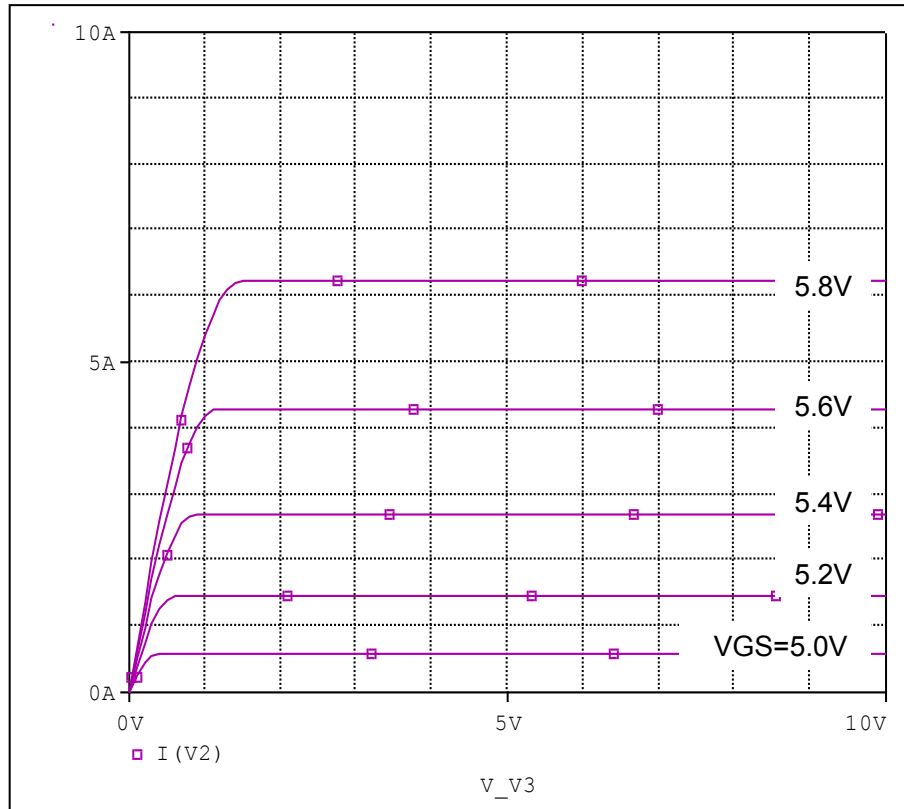


Simulation Result

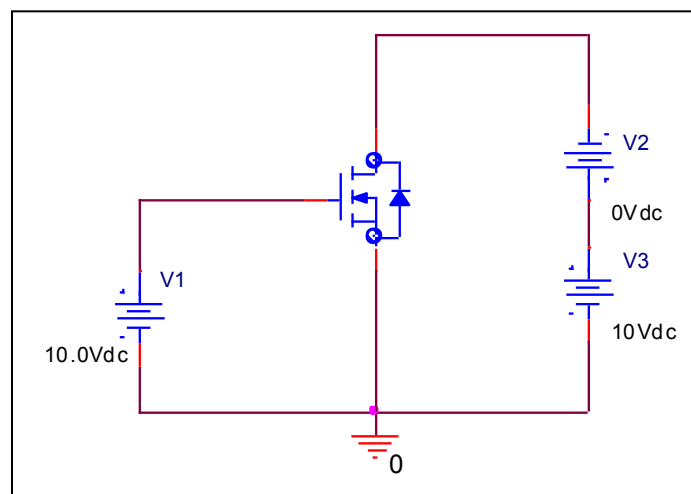
$I_D = 8\text{A}$, $V_{DD} = 48\text{V}$ $V_{GS} = 0/10\text{V}$	Measurement		Simulation		Error(%)
$t_d(\text{on})$	12	ns	12.06	ns	0.5

Output Characteristic

Circuit Simulation result

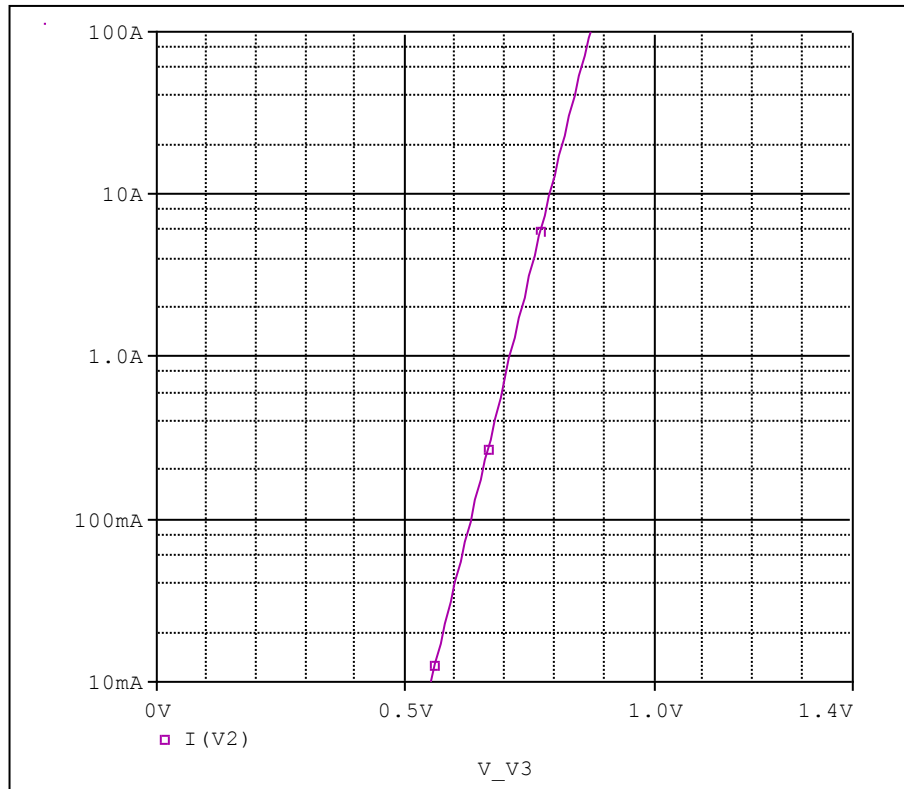


Evaluation circuit

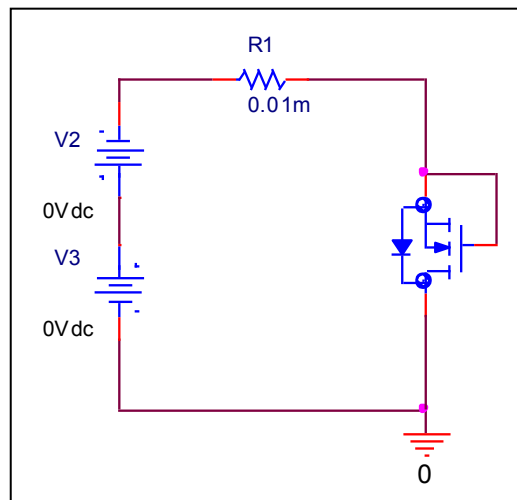


Forward Current Characteristic of Reverse Diode

Circuit Simulation Result

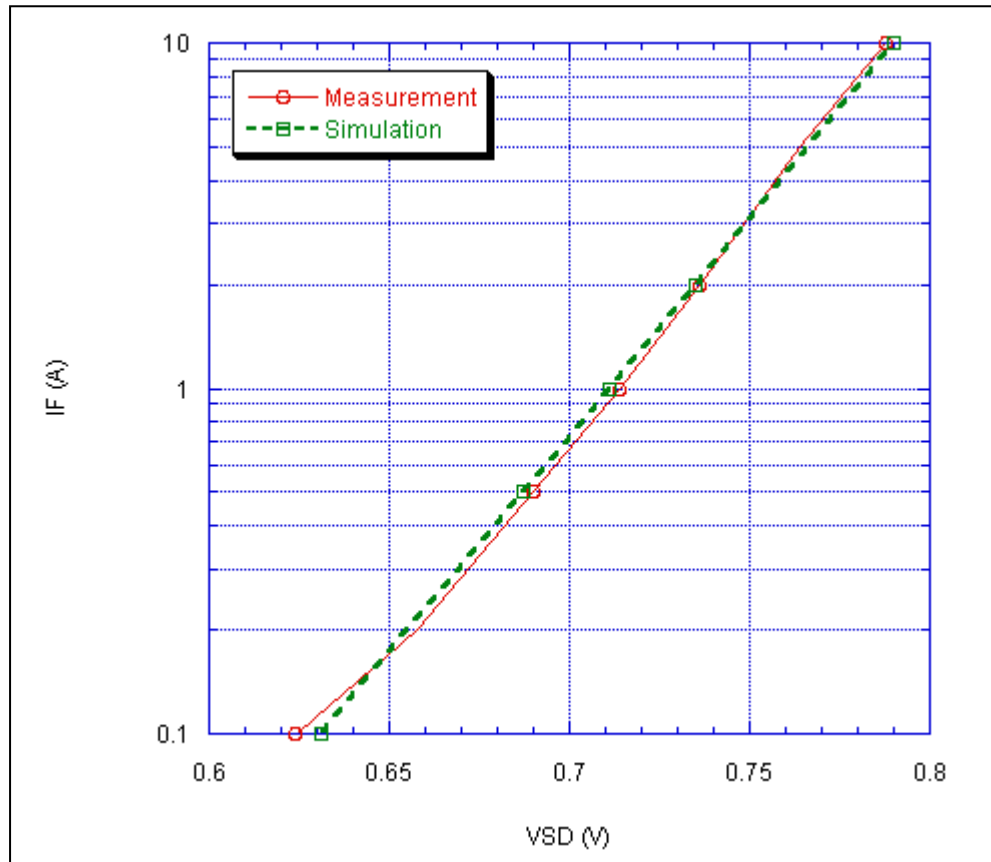


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

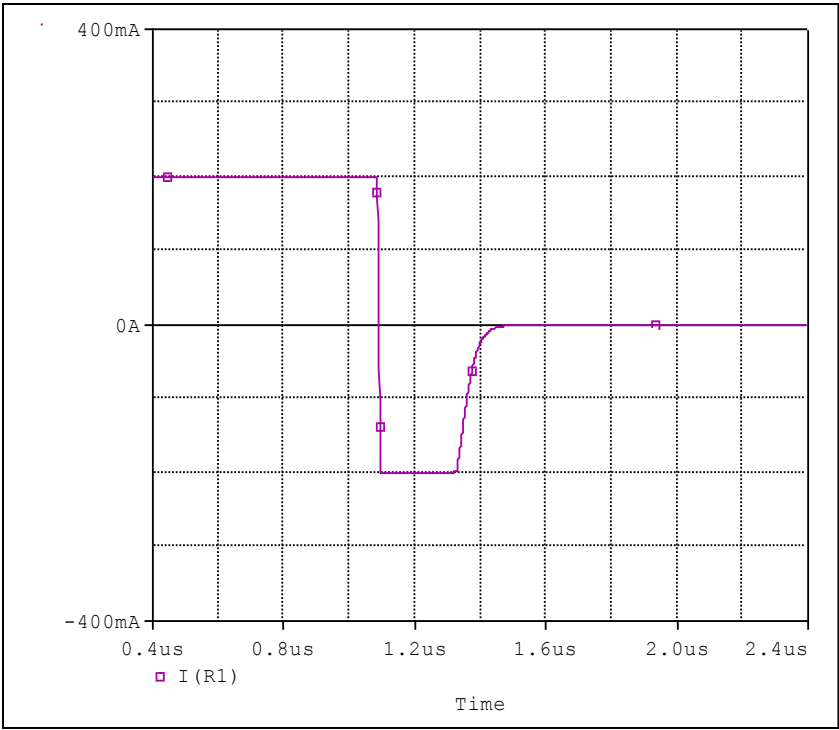


Simulation Result

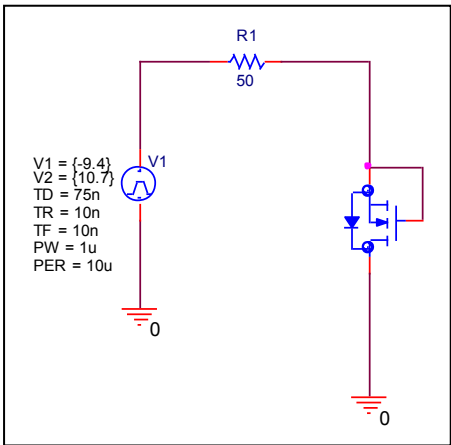
Ifwd(A)	Vfwd(V) Measurement	Vfwd(V) Simulation	%Error
0.100	0.624	0.631	1.090
0.200	0.658	0.655	-0.456
0.500	0.690	0.687	-0.435
1.000	0.714	0.711	-0.420
2.000	0.736	0.735	-0.204
5.000	0.764	0.766	0.262
10.000	0.788	0.790	0.254

Reverse Recovery Characteristic

Circuit Simulation Result



Evaluation Circuit

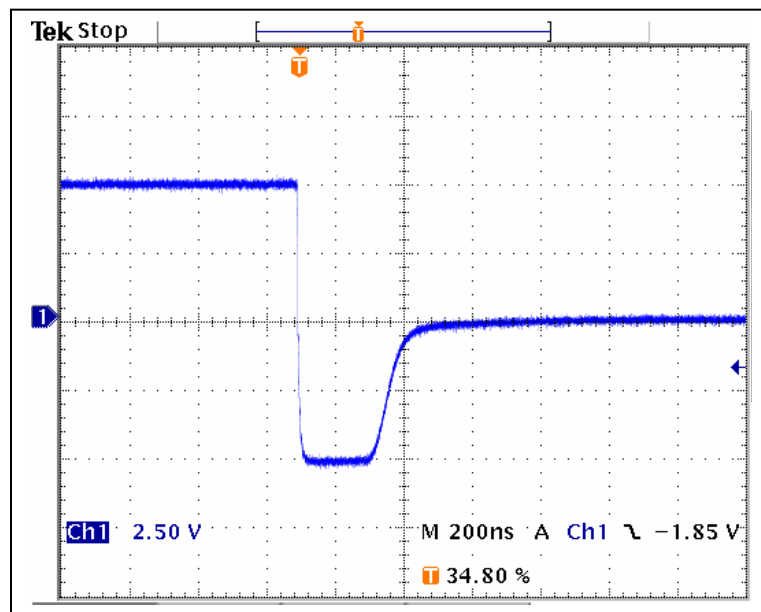


Compare Measurement vs. Simulation

	Measurement		Simulation		Error (%)
$t_{rr}=t_{rj}+t_{rb}$	320	ns	316	ns	1.250

Reverse Recovery Characteristic

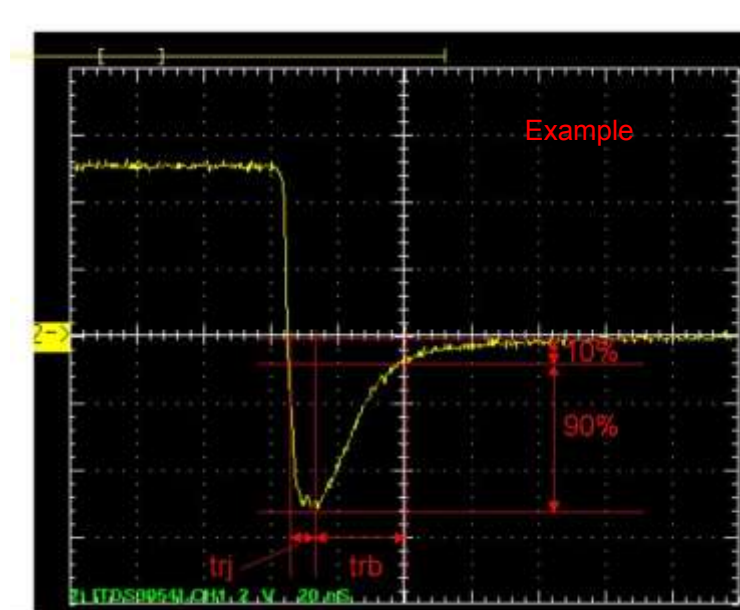
Reference



$Trj=195(ns)$

$Trb=125(ns)$

Conditions: $I_{fwd}=I_{rev}=0.2(A)$, $R_I=50$



Relation between trj and trb